2SK1628, 2SK1629

Silicon N-Channel MOS FET

HITACHI

Application

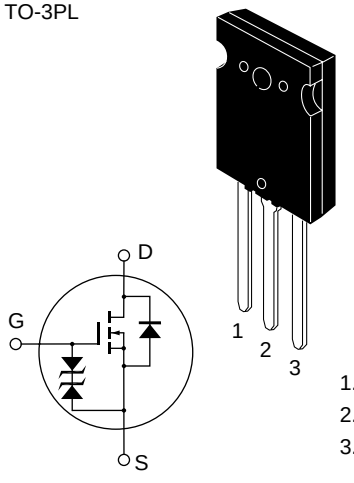
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline

TO-3PL



1. Gate
2. Drain
3. Source

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Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1628	V_{DSS}	450	V
	2SK1629		500	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I_D	30	A
Drain peak current		$I_{D(pulse)}$*[1]	120	A
Body to drain diode reverse drain current		I_{DR}	30	A
Channel dissipation		Pch*[2]	200	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	–55 to +150	°C

Note 1. PW ≤ 10 µs, duty cycle ≤ 1%
2. Value at T_C = 25°C

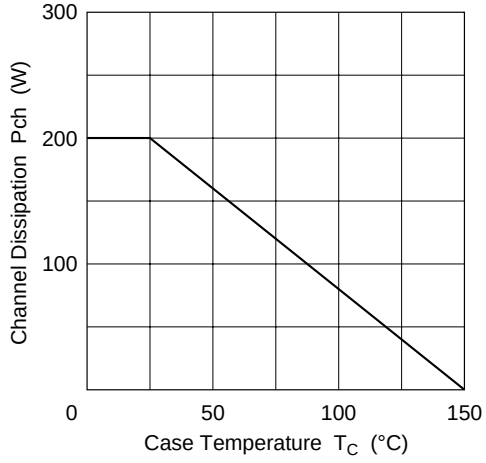
Electrical Characteristics (Ta = 25°C)

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK1628	$V_{(BR)DSS}$	450	—	—	V	I_D = 10 mA, V_{GS} = 0
	2SK1629		500				
Gate to source breakdown voltage		$V_{(BR)GSS}$	±30	—	—	V	I_G = ±100 µA, V_{DS} = 0
Gate to source leak current		I_{GSS}	—	—	±10	µA	V_{GS} = ±25 V, V_{DS} = 0
Zero gate voltage drain current	2SK1628	I_{DSS}	—	—	250	µA	V_{DS} = 360 V, V_{GS} = 0
	2SK1629						V_{DS} = 400 V, V_{GS} = 0
Gate to source cutoff voltage		$V_{GS(off)}$	2.0	—	3.0	V	I_D = 1 mA, V_{DS} = 10 V
Static Drain to source on state resistance	2SK1628	$R_{DS(on)}$	—	0.20	0.25	Ω	I_D = 15 A, V_{GS} = 10 V *[1]
	2SK1629		—	0.22	0.27		
Forward transfer admittance		|yfs|	12	20	—	S	I_D = 15 A, V_{DS} = 10 V *[1]
Input capacitance		Ciss	—	2800	—	pF	V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz
Output capacitance		Coss	—	780	—	pF	
Reverse transfer capacitance		Crss	—	90	—	pF	
Turn-on delay time		$t_{d(on)}$	—	32	—	ns	I_D = 15 A, V_{GS} = 10 V, R_L = 2 Ω
Rise time		t_r	—	140	—	ns	
Turn-off delay time		$t_{d(off)}$	—	200	—	ns	
Fall time		t_f	—	100	—	ns	
Body to drain diode forward voltage		V_{DF}	—	1.1	—	V	I_F = 30 A, V_{GS} = 0
Body to drain diode reverse recovery time		t_{rr}	—	600	—	ns	I_F = 30 A, V_{GS} = 0, di_F/dt = 100 A/µs

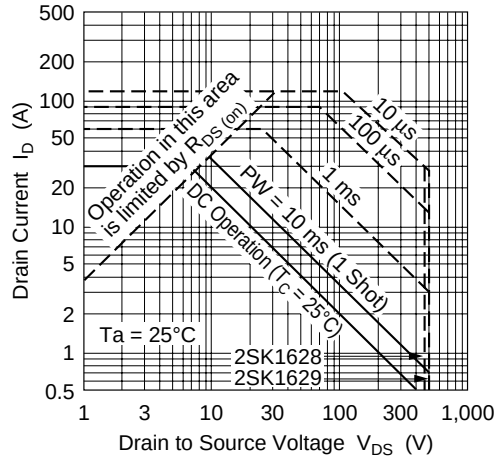
Note 1. Pulse test

See characteristics curves of 2SK1169, 2SK1170

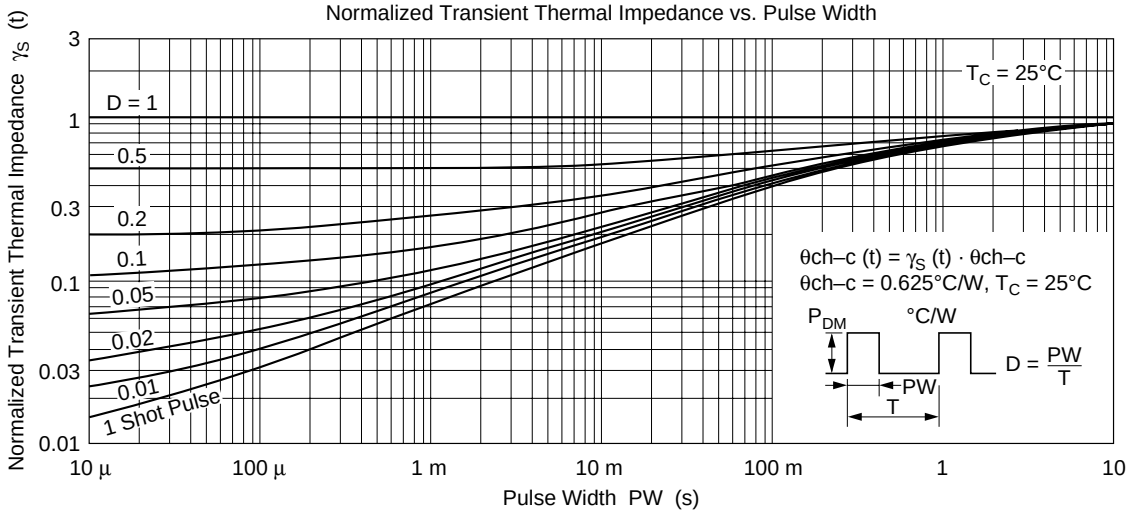
Power vs. Temperature Derating



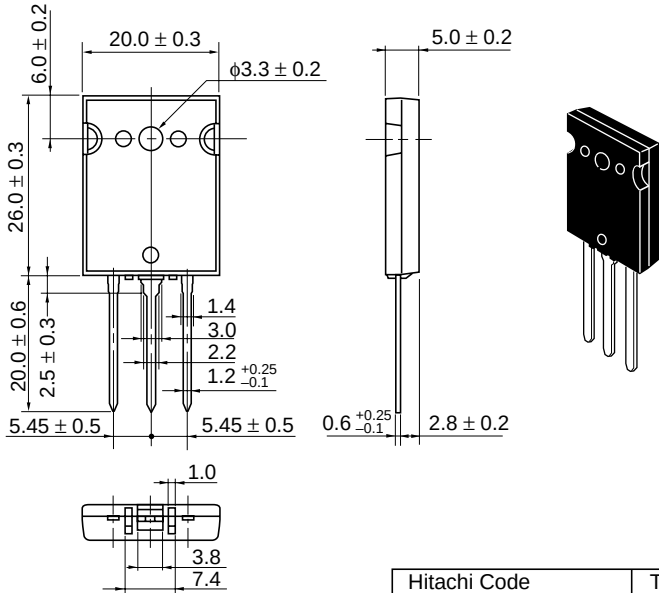
Maximum Safe Operation Area



Normalized Transient Thermal Impedance vs. Pulse Width



Unit: mm



Hitachi Code	TO-3PL
JEDEC	—
EIAJ	—
Weight (reference value)	9.9 g

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HITACHI

Hitachi, Ltd.
Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building. No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX